In This Lecture:

Luttinger-Kohn Hamiltonian

- Refreshment on Defects & Elasticity
- Pikus-Bir Hamiltonian
- Atomic Units

k·p and Similar Band Edge Techniques

Brief Overview

≻Kane's Hamiltonian

8 bands (CB+3 VB with spin) treated exactly

Coupling with the other bands neglected

HH band comes out with wrong sign and value (due above approximation)

No warping predicted (i.e., isotropic) for finite k

Luttinger-Kohn Hamiltonian (for degenerate bands with spin-orbit)

6 VBs treated exactly; can be extended to include CBs as well

Other bands are included via Löwdin's technique

Warping of the VBs is predicted

➢Pikus-Bir Hamiltonian

Just like LK Hamiltonian, but includes the effects of strain in the xtal

FEBRUARY 15, 1955

Luttinger-Kohn Hamiltonian

PHYSICAL REVIEW

VOLUME 97. NUMBER 4

2113 citations! Motion of Electrons and Holes in Perturbed Periodic Fields

J. M. LUTTINGER* AND W. KOHNT Bell Telephone Laboratories, Murray Hill, New Jersey (Received October 13, 1954)

A new method of developing an "effective-mass" equation for electrons moving in a perturbed periodic structure is discussed. This method is particularly adapted to such problems as arise in connection with impurity states and cyclotron resonance in semiconductors such as Si and Ge. The resulting theory generalizes the usual effective-mass treatment to the case where a band minimum is not at the center of the Brillouin zone, and also to the case where the band is degenerate. The latter is particularly striking, the usual Wannier equation being replaced by a set of coupled differential equations.

Begin with the total Hamiltonian for the cell-periodic fn's dropping their band { indices for convenience:

$$Hu_{\mathbf{k}}(\mathbf{r}) = E(\mathbf{k})u_{\mathbf{k}}(\mathbf{r})$$

$$H = H_{0} + \frac{\hbar^{2}k^{2}}{2m_{0}} + \frac{\hbar}{4m_{0}^{2}c^{2}}\nabla V \times \mathbf{p} \cdot \boldsymbol{\sigma} + H'$$
Neglect
compared to
$$H_{0} = \frac{p^{2}}{2m} + V(\mathbf{r})$$

$$H' = \frac{\hbar}{m_{0}}\mathbf{k} \cdot \Pi$$

$$\Pi = \mathbf{p} + \frac{\hbar}{4m_{0}c^{2}}\boldsymbol{\sigma} \times \nabla V$$

Expand any cell-periodic wf in terms of the **k**=0 basis:

$$u_{\mathbf{k}}(\mathbf{r}) = \sum_{j'}^{A} a_{j'}(\mathbf{k}) u_{j'0}(\mathbf{r}) + \sum_{\gamma}^{B} a_{\gamma}(\mathbf{k}) u_{\gamma 0}(\mathbf{r})$$

where, according to Kane's model **k**=0 solutions (exc. Class B) are of the form:

$$u_{10}(\mathbf{r}) = \left|\frac{3}{2}, \frac{3}{2}\right\rangle = \frac{-1}{\sqrt{2}} \left| (X + iY) \uparrow \right\rangle$$

$$u_{20}(\mathbf{r}) = \left|\frac{3}{2}, \frac{1}{2}\right\rangle = \frac{-1}{\sqrt{6}} \left| (X + iY) \downarrow \right\rangle + \sqrt{\frac{2}{3}} \left| Z \uparrow \right\rangle$$

$$u_{30}(\mathbf{r}) = \left|\frac{3}{2}, \frac{-1}{2}\right\rangle = \frac{1}{\sqrt{6}} \left| (X - iY) \uparrow \right\rangle + \sqrt{\frac{2}{3}} \left| Z \downarrow \right\rangle$$

$$u_{40}(\mathbf{r}) = \left|\frac{3}{2}, \frac{-3}{2}\right\rangle = \frac{1}{\sqrt{2}} \left| (X - iY) \downarrow \right\rangle$$

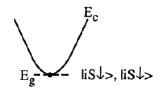
$$u_{50}(\mathbf{r}) = \left|\frac{1}{2}, \frac{1}{2}\right\rangle = \frac{1}{\sqrt{3}} \left| (X + iY) \downarrow \right\rangle + \frac{1}{\sqrt{3}} \left| Z \uparrow \right\rangle$$

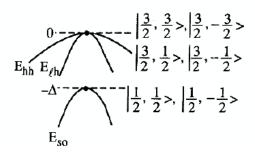
$$u_{60}(\mathbf{r}) = \left|\frac{1}{2}, \frac{-1}{2}\right\rangle = \frac{1}{\sqrt{3}} \left| (X - iY) \uparrow \right\rangle - \frac{1}{\sqrt{3}} \left| Z \downarrow \right\rangle$$

Also recall that at $\mathbf{k}=0$, band edge fn's satisy:

$$H(\mathbf{k}=0)u_{j0}(\mathbf{r})=E_j(0)u_{j0}(\mathbf{r})$$

$$E_j(0) = E_p + \frac{\Delta}{3} = 0$$
 for $j = 1, 2, 3, 4$
 $E_j(0) = E_p - \frac{2\Delta}{3} = -\Delta$ for $j = 5, 6$





where $E_p = -\Delta/3$

Now, apply Löwdin's method:

$$\sum_{j'}^{A} \left(U_{jj'}^{A} - E\delta_{jj'} \right) a_{j'}(\mathbf{k}) = 0$$

Effect of remote
bands are here

where

$$\begin{split} U_{jj'}^{A} &= H_{jj'} + \sum_{\gamma \neq j, j'}^{B} \frac{H_{j\gamma} H_{\gamma j'}}{E_0 - E_{\gamma}} = H_{jj'} + \sum_{\gamma \neq j, j'}^{B} \frac{H_{j\gamma}' H_{\gamma j'}}{E_0 - E_{\gamma}} \\ H_{jj'} &= \left\langle u_{j0} | H | u_{j'0} \right\rangle = \left[E_j(0) + \frac{\hbar^2 k^2}{2m_0} \right] \delta_{jj'} \qquad (j, j' \in A) \\ H_{j\gamma}' &= \left\langle u_{j0} | \frac{\hbar}{m_0} \mathbf{k} \cdot \mathbf{H} | u_{\gamma 0} \right\rangle \cong \sum_{\alpha} \frac{\hbar k_{\alpha}}{m_0} p_{j\gamma}^{\alpha} \qquad (j \in A, \gamma \notin A) \end{split}$$

where we note that $\Pi_{jj'} = 0$, for $j, j' \in A$, and $\Pi_{j\gamma}^{\alpha} = p_{j\gamma}^{\alpha}$ for $j \in A$ and $\gamma \notin A$. Since $\gamma \neq j$, adding the unperturbed part to the perturbed part in $H'_{j\gamma}$ does not affect the results, i.e., $H_{j\gamma} = H'_{j\gamma}$. We thus obtain

$$U_{jj'}^{A} = \left[E_{j}(0) + \frac{\hbar^{2}k^{2}}{2m_{0}} \right] \delta_{jj'} + \frac{\hbar^{2}}{m_{0}^{2}} \sum_{\gamma \neq j, \, j'}^{B} \sum_{\alpha, \, \beta} \frac{k_{\alpha}k_{\beta}p_{j\gamma}^{\alpha}p_{\gamma j'}^{\beta}}{E_{0} - E_{\gamma}}$$

couples bands *j* and *j*'

Change of notation; let $U_{jj'}^A \equiv D_{jj'}$ via band γ in class B Ref: Chuang

$$D_{jj'} = E_j(0) \, \delta_{jj'} + \sum_{lpha, eta} D_{jj'}^{lphaeta} k_{lpha} k_{eta}$$

where
$$D_{jj'}^{\alpha\beta} = \frac{\hbar^2}{2m_0} \left[\delta_{jj'} \delta_{\alpha\beta} + \sum_{\gamma}^{B} \frac{p_{j\gamma}^{\alpha} p_{\gamma j'}^{\beta} + p_{j\gamma}^{\beta} p_{\gamma j'}^{\alpha}}{m_0 (E_0 - E_\gamma)} \right]$$

For *j=j*', similar to single-band effective mass tensor

The couplings within class A can be expressed using three so-called Luttinger parameters: γ_1 , γ_2 , γ_3

They are actually fitted to experimental data to generate faithful band dispersions

In terms of Luttinger parameters, the LK Hamiltonian becomes:

$$\overline{\overline{\mathbf{H}}}^{\mathrm{LK}} = -\begin{bmatrix} P+Q & -S & R & 0 & -S/\sqrt{2} & \sqrt{2}R \\ -S^{+} & P-Q & 0 & R & -\sqrt{2}Q & \sqrt{3/2}S \\ R^{+} & 0 & P-Q & S & \sqrt{3/2}S^{+} & \sqrt{2}Q \\ 0 & R^{+} & S^{+} & P+Q & -\sqrt{2}R^{+} & -S^{+}/\sqrt{2} \\ -S^{+}/\sqrt{2} & -\sqrt{2}Q^{+} & \sqrt{3/2}S & -\sqrt{2}R & P+\Delta & 0 \\ \sqrt{2}R^{+} & \sqrt{3/2}S^{+} & \sqrt{2}Q^{+} & -S/\sqrt{2} & 0 & P+\Delta \end{bmatrix}$$
HH BO

complex conjugate

where

$$P = \frac{\hbar^2 \gamma_1}{2m_0} \left(k_x^2 + k_y^2 + k_z^2 \right)$$
$$Q = \frac{\hbar^2 \gamma_2}{2m_0} \left(k_x^2 + k_y^2 - 2k_z^2 \right)$$
$$R = \frac{\hbar^2}{2m_0} \left[-\sqrt{3} \gamma_2 \left(k_x^2 - k_y^2 \right) + i2\sqrt{3} \gamma_3 k_x k_y \right]$$

$$S = \frac{\hbar^2 \gamma_3}{m_0} \sqrt{3} \left(k_x - \mathrm{i} k_y \right) k_z$$

So, essentially we have solved the Hamiltonian

$$\left[\frac{p^2}{2m_0} + V(\mathbf{r}) + \frac{\hbar}{4m_0^2c^2}\nabla V \times \mathbf{p} \cdot \boldsymbol{\sigma}\right]\psi_{n\mathbf{k}}(\mathbf{r}) = E_n(\mathbf{k})\psi_{n\mathbf{k}}(\mathbf{r})$$

where

6

$$\psi_{n\mathbf{k}}(\mathbf{r}) = \mathrm{e}^{\mathrm{i}\mathbf{k}\cdot\mathbf{r}}u_{n\mathbf{k}}(\mathbf{r}) \qquad u_{n\mathbf{k}}(\mathbf{r}) = \sum_{j=1}^{6} a_j(\mathbf{k})u_{j0}(\mathbf{r})$$

For the expansion eigenvectors and eigenvalues:

$$\sum_{j'=1}^{\circ} H_{jj'}^{\mathrm{LK}} a_{j'}(\mathbf{k}) = E a_j(\mathbf{k}) \qquad \qquad E_n(\mathbf{k}) = E$$

But now, the effect of remote bands are also taken into account through the Löwdin renormalization. It reveals indirect band couplings among those within class A via direct couplings with those in class B.

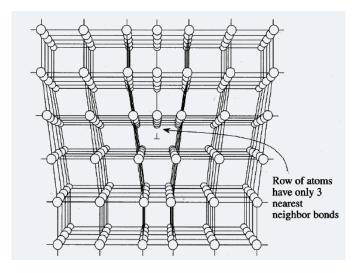
Common defects in semiconductors

Point defects

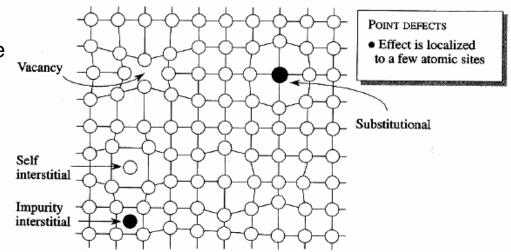
A function of the xtal growth temperature

$$\frac{N_d}{N_{sot}} = k_d \exp(-\frac{E_d}{k_B T_{growth}})$$

>Line defects (dislocations)



Planar & volume defects Important in poly-xtalline mat'ls



Strain in heterostructures

Strain:
$$\varepsilon = \frac{a_s - a_L}{a_L}$$

A simplistic estimate of the critical thickness:

$$d_{\varepsilon} \cong \frac{a_{\mathcal{S}}}{2|\varepsilon|}$$

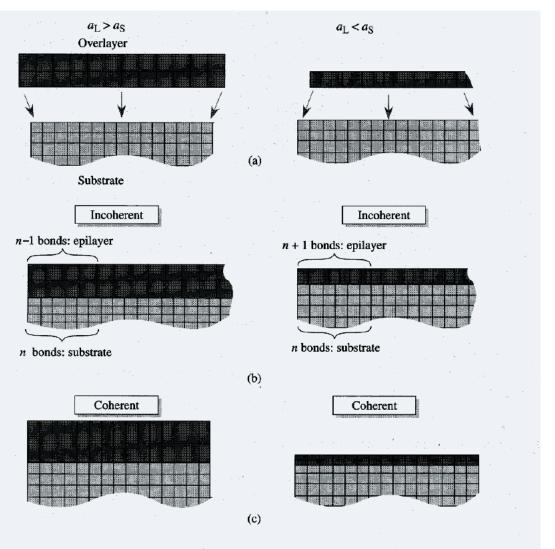
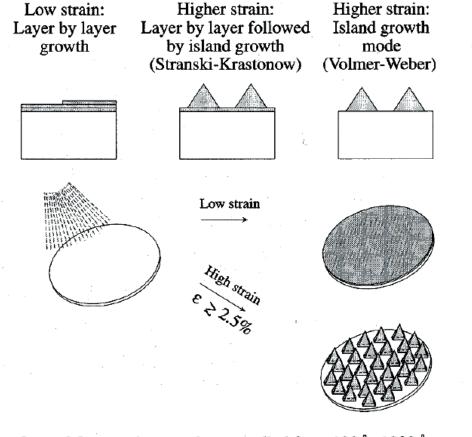


Figure 1.20: (a) The conceptual exercise in which an overlayer with one lattice constant is placed without distortion on a substrate with a different lattice constant. (b) Dislocations are generated at positions where the interface bonding is lost. (c) The case is shown where the overlayer is distorted so that no dislocation is generated.

Ref: Singh

Self-assembled structures



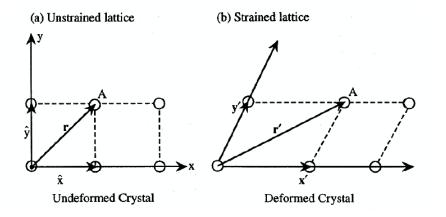
Lateral feature sizes can be controlled from 100Å -1000Å $\implies 10^{12}$ features per wafer can be produced without lithography

Figure 1.22: Growth modes in strained epitaxy. The island mode growth can be exploited to make "self-assembled" quantum dot structures.

Ref: Singh

Some background on elasticity

Strain & volume dilation



$$\mathbf{x}' = (1 + \varepsilon_{xx})\hat{x} + \varepsilon_{xy}\hat{y} + \varepsilon_{xz}\hat{z}$$
$$\mathbf{y}' = \varepsilon_{yx}\hat{x} + (1 + \varepsilon_{yy})\hat{y} + \varepsilon_{yz}\hat{z}$$
$$\mathbf{z}' = \varepsilon_{zx}\hat{x} + \varepsilon_{zy}\hat{y} + (1 + \varepsilon_{zz})\hat{z}$$

No longer unit vectors

We define six independent components of strain

$$e_{1} = \varepsilon_{xx} \qquad e_{2} = \varepsilon_{yy} \qquad e_{3} = \varepsilon_{zz}$$

$$e_{4} = \mathbf{x}' \cdot \mathbf{y}' = \varepsilon_{xy} + \varepsilon_{yx}$$

$$e_{5} = \mathbf{y}' \cdot \mathbf{z}' = \varepsilon_{yz} + \varepsilon_{zy}$$

$$e_{6} = \mathbf{z}' \cdot \mathbf{x}' = \varepsilon_{zx} + \varepsilon_{xz}$$

Another common notation

 e_{xx} , e_{yy} , e_{zz} , e_{xy} , e_{yz} , e_{zx}

Strain & volume dilation (cont'd)

$$\mathbf{r} = x\hat{x} + y\hat{y} + z\hat{z} \equiv (x, y, z)$$

$$\mathbf{r}' = x\,\mathbf{x}' + y\,\mathbf{y}' + z\,\mathbf{z}'$$

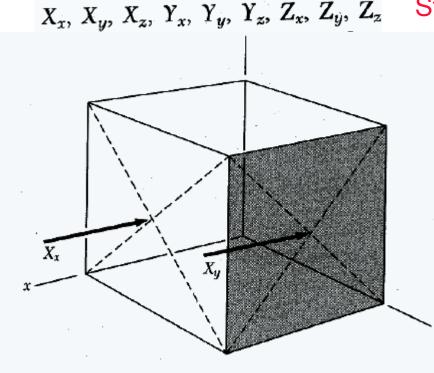
$$\mathbf{r}' = x'\hat{x} + y'\hat{y} + z'\hat{z} \equiv (x', y', z')$$

$$\frac{V + \delta V}{V} = \mathbf{x}' \cdot \mathbf{y}' \times \mathbf{z}' = 1 + (\varepsilon_{xx} + \varepsilon_{yy} + \varepsilon_{zz})$$

$$\frac{\delta V}{V} = \varepsilon_{xx} + \varepsilon_{yy} + \varepsilon_{zz}$$

Fractional change of xtal volume under uniform deformation

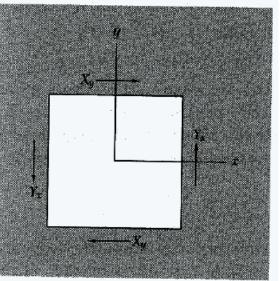
Some background on elasticity (cont'd) Stress



Under static equilibrium (total torque around origin should vanish)

$$Y_z = Z_y ; \qquad Z_x = X_z ; \qquad X_y = Y_x$$

Stress components in general



Ref: Kittel

Some background on elasticity (cont'd)

Six independent components can be chosen as: X_x , Y_y , Z_z , Y_z , Z_x , X_y

Stress-Strain relation: extension of Hooke's law (linear regime)

$$\begin{aligned} X_x &= C_{11}e_{xx} + C_{12}e_{yy} + C_{13}e_{zz} + C_{14}e_{yz} + C_{15}e_{zx} + C_{16}e_{xy} \\ Y_y &= C_{21}e_{xx} + C_{22}e_{yy} + C_{23}e_{zz} + C_{24}e_{yz} + C_{25}e_{zx} + C_{26}e_{xy} \\ Z_z &= C_{31}e_{xx} + C_{32}e_{yy} + C_{33}e_{zz} + C_{34}e_{yz} + C_{35}e_{zx} + C_{36}e_{xy} \\ Y_z &= C_{41}e_{xx} + C_{42}e_{yy} + C_{43}e_{zz} + C_{44}e_{yz} + C_{45}e_{zx} + C_{46}e_{xy} \\ Z_x &= C_{51}e_{xx} + C_{52}e_{yy} + C_{53}e_{zz} + C_{54}e_{yz} + C_{55}e_{zx} + C_{56}e_{xy} \\ X_y &= C_{61}e_{xx} + C_{62}e_{yy} + C_{63}e_{zz} + C_{64}e_{yz} + C_{65}e_{zx} + C_{66}e_{xy} \end{aligned}$$

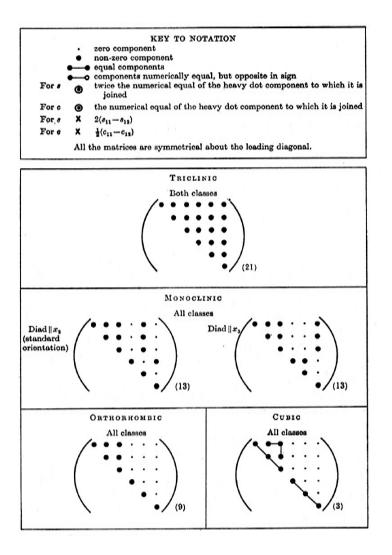
C's : elastic stiffness constants, moduli of elasticity

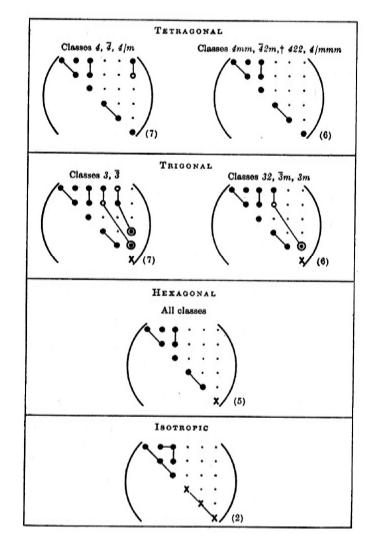
For a cubic xtal:

	e_{xx}	e_{yy}	e_{zz}	e_{yz}	e_{zr}	e_{xy}
X _x	C_{11}	C ₁₂	C_{12}	0	0	0
Yy	C_{12}	C_{11}	C_{12}	0	0	0
Z_z	C_{12}	C_{12}	C_{11}	0	0	0
Y_z	0	0	0	C_{44}	0	0
Z_x	0	0	0	0	C_{44}	0
Xy	0	0	0	0	0	C ₄₄

Ref: Kittel

Effects of xtal symmetry on elastic constants





Ref: Nye

Back to pseudomorphic epitaxial growth

$$e_{\parallel} = rac{a_S}{a_L} - 1$$

= ϵ

No stress along the growth direction!

$$\epsilon_{xx} = \epsilon_{\parallel}$$

$$\epsilon_{yy} = \epsilon_{xx}$$

$$\epsilon_{zz} = \frac{-2c_{12}}{c_{11}}\epsilon_{\parallel}$$

$$\epsilon_{xy} = 0$$

$$\epsilon_{yz} = 0$$

$$\epsilon_{zx} = 0$$

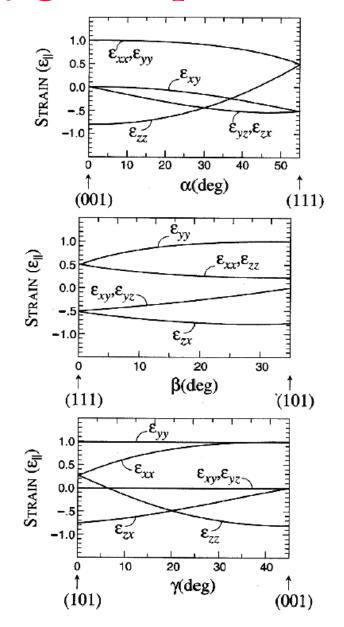
For strained growth on (001) substrate & fcc lattice

For strained growth on

(111) substrate & fcc lattice

$$\begin{aligned} \epsilon_{xx} &= \left[\frac{2}{3} - \frac{1}{3} \left(\frac{2c_{11} + 4c_{12} - 4c_{44}}{c_{11} + 2c_{12} + 4c_{44}}\right)\right] \epsilon_{\parallel} \\ \epsilon_{yy} &= \epsilon_{xx} \\ \epsilon_{zz} &= \epsilon_{xx} \\ \epsilon_{xy} &= \left[\frac{-1}{3} - \frac{1}{3} \left(\frac{2c_{11} + 4c_{12} - 4c_{44}}{c_{11} + 2c_{12} + 4c_{44}}\right)\right] \epsilon_{\parallel} \\ \epsilon_{yz} &= \epsilon_{xy} \\ \epsilon_{zx} &= \epsilon_{yz} \end{aligned}$$
Ref: Singh

On arbitrary growth planes



Strained tensor for self-organized quantum dots

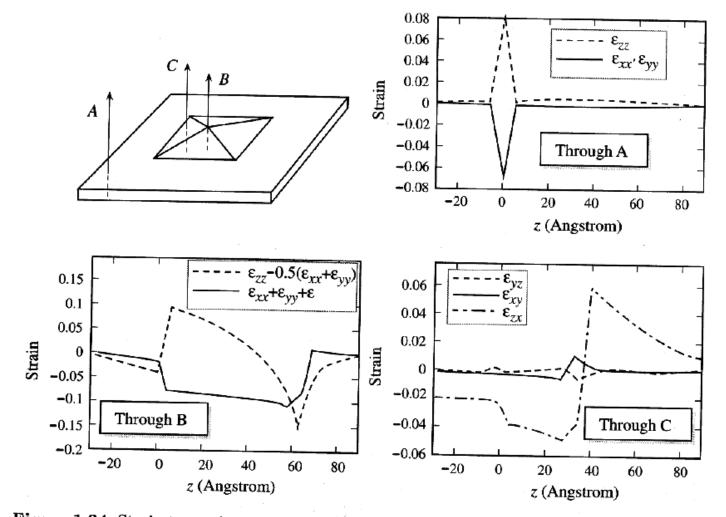
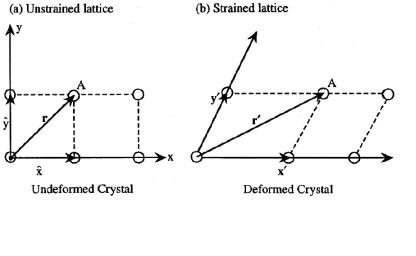


Figure 1.24: Strain tensor in a pyramidal InAs on GaAs self-assembled quantum dot.

Ref: Singh

Pikus-Bir Hamiltonian: Including Strain

Uniformly deformed crystal



$$\mathbf{x}' = (1 + \varepsilon_{xx})\hat{x} + \varepsilon_{xy}\hat{y} + \varepsilon_{xz}\hat{z}$$
$$\mathbf{y}' = \varepsilon_{yx}\hat{x} + (1 + \varepsilon_{yy})\hat{y} + \varepsilon_{yz}\hat{z}$$
$$\mathbf{z}' = \varepsilon_{zx}\hat{x} + \varepsilon_{zy}\hat{y} + (1 + \varepsilon_{zz})\hat{z}$$

No longer unit vectors

invert

$$\mathbf{r}' = \mathbf{r} + \overline{\overline{\varepsilon}} \cdot \mathbf{r} = (1 + \overline{\overline{\varepsilon}}) \cdot \mathbf{r}$$

$$r_i = r'_i - \sum_j \varepsilon_{ij} r'_j$$

$$\mathbf{r} = (1 - \overline{\overline{\varepsilon}}) \cdot \mathbf{r}'$$

Back in the deformed xtal coordinate system: $\left[\frac{\mathbf{p}^{\prime 2}}{2m_0} + V(\mathbf{r}^{\prime})\right]\psi_{n\mathbf{k}^{\prime}}(\mathbf{r}^{\prime}) = E_n(\mathbf{k}^{\prime})\psi_{n\mathbf{k}^{\prime}}(\mathbf{r}^{\prime})$

Now comes some manipulations

[

using the chain rule
$$\frac{\partial}{\partial r'_i} = \sum_j \frac{\partial r_j}{\partial r'_i} \frac{\partial}{\partial r_j} = \frac{\partial}{\partial r_i} - \sum_j \varepsilon_{ji} \frac{\partial}{\partial r_j}$$

therefore
$$\mathbf{p}' = \mathbf{p} \cdot (1 - \overline{\overline{\varepsilon}})$$
 $p'^2 = p^2 - 2\sum_{i,j} p_i \varepsilon_{ij} p_j$

expanding the potential $V[(1+\overline{\overline{\varepsilon}})\cdot\mathbf{r}] = V_0(\mathbf{r}) + \sum_{i,j} V_{ij}\varepsilon_{ij}$ $V_{ij} = \frac{\partial V}{\partial \varepsilon_{ij}}\Big|_{\varepsilon_{ij} \to 0}$

$$H_{0} + H_{\varepsilon}]\psi_{nk'} [(1 + \bar{\varepsilon}) \cdot \mathbf{r}] = E_{n}(\mathbf{k}')\psi_{nk'} [(1 + \bar{\varepsilon}) \cdot \mathbf{r}]$$

$$H_{0} = \frac{p^{2}}{2m_{0}} + V_{0}(\mathbf{r})$$

$$H_{\varepsilon} \equiv \sum_{\alpha,\beta} \hat{D}^{\alpha\beta} \varepsilon_{\alpha\beta} = \sum_{\alpha,\beta} \left(-\frac{1}{m_{0}} p_{\alpha} p_{\beta} + V_{\alpha\beta} \right) \varepsilon_{\alpha\beta}$$

$$\psi_{nk'} [(1 + \bar{\varepsilon}) \cdot \mathbf{r}] = e^{i\mathbf{k}' \cdot \mathbf{r}'} u_{nk'}(\mathbf{r}')$$

$$= e^{i\mathbf{k}' \cdot (1 + \bar{\varepsilon}) \cdot \mathbf{r}} u_{nk'} [(1 + \bar{\varepsilon}) \cdot \mathbf{r}]$$

$$= e^{i\mathbf{k} \cdot \mathbf{r}} u_{nk'} [(1 + \bar{\varepsilon}) \cdot \mathbf{r}]$$

Arriving at the Pikus-Bir Hamiltonian

$$H_0[e^{i\mathbf{k}\cdot\mathbf{r}}u_{n\mathbf{k}}^s(\mathbf{r})] = e^{j\mathbf{k}\cdot\mathbf{r}}\left(H_0 + \frac{\hbar}{m_0}\mathbf{k}\cdot\mathbf{p} + \frac{\hbar^2k^2}{2m_0}\right)u_{n\mathbf{k}}^s(\mathbf{r})$$
$$H_\varepsilon[e^{i\mathbf{k}\cdot\mathbf{r}}u_{n\mathbf{k}}^s(\mathbf{r})] = e^{i\mathbf{k}\cdot\mathbf{r}}\left(H_\varepsilon - \frac{2\hbar}{m_0}\sum_{\alpha,\beta}k_\alpha\varepsilon_{\alpha\beta}p_\beta\right)u_{n\mathbf{k}}^s(\mathbf{r})$$

$$[H_{0} + H']u_{n\mathbf{k}}^{s}(\mathbf{r}) = \left(E - \frac{\hbar^{2}k^{2}}{2m_{0}}\right)u_{n\mathbf{k}}^{s}(\mathbf{r})$$
$$H' = H_{k} + H_{e} + H_{ek}$$
$$H_{k} = \frac{\hbar}{m_{0}}\mathbf{k} \cdot \mathbf{p}$$
$$H_{e} = \sum_{\alpha,\beta} \hat{D}^{\alpha\beta}\varepsilon_{\alpha\beta}$$
$$H_{ek} \equiv -2\frac{\hbar}{m_{0}}\sum_{\alpha,\beta}k_{\alpha}\varepsilon_{\alpha\beta}p_{\beta}$$

correspondence with LK Hamiltonian: $k_{\alpha}k_{\beta} \leftrightarrow \varepsilon_{\alpha\beta}$

keeping terms to second order in **k** and first order $H = H^{LK} + H_{\varepsilon}$ $(H_{\varepsilon})_{jj'} = \sum_{\alpha,\beta} \hat{D}_{jj'}^{\alpha\beta} \varepsilon_{\alpha\beta}$ in strain reduces to in strain reduces to Pikus-Bir CB For the CB: $\frac{\hbar^2}{2m_e^*} \leftrightarrow a_c$ (isotropic case) deformation $E(\mathbf{k}) = E_c(0) + \frac{\hbar^2}{2} \sum_{\alpha,\beta} \left(\frac{1}{m^*}\right)_{\alpha\beta} k_{\alpha} k_{\beta} + a_c(\varepsilon_{xx} + \varepsilon_{yy} + \varepsilon_{zz})$ For the VB: $\begin{pmatrix}
\frac{\hbar^2 \gamma_1}{2m_0} \leftrightarrow D_v^d = -a_v \\
\frac{\hbar^2 \gamma_2}{2m_0} \leftrightarrow \frac{D_u}{3} = -\frac{b}{2} \\
\frac{\hbar^2 \gamma_3}{2m_0} \leftrightarrow \frac{D_u'}{3} = \frac{-d}{2\sqrt{3}}$

The final form including strain
$$H = -\begin{bmatrix} P+Q & -S & R & 0 & -\frac{1}{\sqrt{2}}S & \sqrt{2}R \\ -S^{+} & P-Q & 0 & R & -\sqrt{2}Q & \sqrt{\frac{3}{2}}S \\ R^{+} & 0 & P-Q & S & \sqrt{\frac{3}{2}}S^{+} & \sqrt{2}Q \\ 0 & R^{+} & S^{+} & P+Q & -\sqrt{2}R^{+} & -\frac{1}{\sqrt{2}}S^{+} \\ -\frac{1}{\sqrt{2}}S^{+} & -\sqrt{2}Q & \sqrt{\frac{3}{2}}S & -\sqrt{2}R & P+\Delta & 0 \\ \sqrt{2}R^{+} & \sqrt{\frac{3}{2}}S^{+} & \sqrt{2}Q & -\frac{1}{\sqrt{2}}S & 0 & P+\Delta \end{bmatrix} \begin{vmatrix} \frac{1}{2}, -\frac{1}{2} \\ \frac{1}{2} \\ \frac{1}{2}, -\frac{1}{$$

C. Bulutay

Topics on Semiconductor Physics ant Band Structure Parameters^{a-f}

Lecture 5

Table K.2	Important Band Structure Parameters ^{*-}
for GaAs,	AlAs, InAs, InP, and GaP

	Materials							
	GaAs	AlAs	InAs	InP	GaP			
Parameters								
a_0 (Å)	5.6533	5.6600	6.0584	5.8688	5.4505			
$E_g(eV)$								
0 K	1.519	3.13	0.42	1.424	2.90			
		2.229*			2.35*			
300 K	1.424	3.03	0.354	1.344	2.78			
		2.168*			2.27*			
$\Delta (eV)$	0.34	0.28	0.38	0.11	0.08			
$E_{v, av}$ (eV)	-6.92	-7.49	-6.67	-7.04	-7.40			
Optical matrix	25.7	21.1	22.2	20.7	22.2			
parameter E_p (eV)	(25.0) ^f			(16.7) ^f				
Deformation potentials (eV)								
$a_c (eV)$	-7.17	-5.64	-5.08	-5.04	-7.14			
$a_{e}(eV)$	1.16	2.47	1.00	1.27	1.70			
$a = a_c - a_v$ (eV)	-8.33	-8.11	-6.08	-6.31	-8.83			
b (eV)	-1.7	-1.5	-1.8	-1.7	-1.8			
$d(\mathbf{eV})$	-4.55	-3.4	-3.6	-5.6	-4.5			
C_{11} (10 ¹¹ dyne/cm ²)	11.879	12.5	8.329	10.11	14.05			
C_{12} (10 ¹¹ dyne/cm ²)	5.376	5.34	4.526	5.61	6.203			
C_{44} (10 ¹¹ dyne/cm ²)	5.94	5.42	3.96	4.56	7.033			
Effective masses								
m_{e}^{*}/m_{0}	0.067	0.15	0.023	0.077	0.25			
m_{hh}^*/m_0	0.50	0.79	0.40	0.60	0.67			
m_{lh}^*/m_0	0.087	0.15	0.026	0.12	0.17			
$m_{hh,z} / m_0 = \frac{1}{\gamma_1 - 2\gamma_2}$ $m_{th,z} / m_0 = \frac{1}{\gamma_1 + 2\gamma_2}$	0.333	0.478	0.263	0.606	0.326			
$m_{th,z}/m_0 = \frac{1}{\gamma_1 + 2\gamma_2}$	0.094	0.208	0.027	0.121	0. 19 9			
γ1	6.8 (6.85)	3.45	20.4	4.95	4.05			
Y2	1.9 (2.1)	0.68	8.3	1.65	0.49			
73	2.73 (2.9)	1.29	9.1	2.35	1.25			

(Hartree) Atomic Units

In any computational project on semiconductors, use atomic units (a.u.), not cgs/SI

cgs (Gaussian) \rightarrow Atomic Units:

Set in expressions:
$$e=m_0=\hbar=1$$

SI → Atomic Units:

Set in expressions: $\frac{e}{\sqrt{4\pi\epsilon_0}} = m_0 = \hbar = 1$

Derived Units in a.u. :

Energy: 1 Ha = 2 Ry = 27.12 eV Length: 1 a_B = Bohr Radius

Demonstration on Schrödinger Eq.

Start with the following expression in SI for the exciton bound states

$$\left[-\frac{\hbar^2}{2\mu_X}\nabla^2 - \frac{e^2}{4\pi\kappa\varepsilon_0 r}\right]\psi_X(\vec{r}) = E\psi_X(\vec{r})$$

Setting above:
$$\frac{e}{\sqrt{4\pi\varepsilon_0}} = m_0 = \hbar = 1$$

Results in the expression in terms of variables in a.u. (denoted with tilde)

$$\left[-\frac{1}{2\tilde{\mu}_{X}}\tilde{\nabla}^{2}-\frac{1}{\kappa\tilde{r}}\right]\tilde{\psi}_{X}(\vec{\tilde{r}})=\tilde{E}\tilde{\psi}_{X}(\vec{\tilde{r}})$$